John L

	Application No.	Applicant(s)
Notice of Allowability		
	10/766,645 Examiner	CHOI ET AL.
	Heather A. Doty	2813
The MAILING DATE of this communication appeal claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in or other appropriate comming IGHTS. This application is:	n this application. If not included unication will be mailed in due course. THIS
1. \boxtimes This communication is responsive to <u>the amendment date</u>	d 9/28/2005.	
2. The allowed claim(s) is/are 1-21.		
 3. Acknowledgment is made of a claim for foreign priority unerstanding a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 		or (f).
2. ☐ Certified copies of the priority documents have		on No.
Copies of the certified copies of the priority do	· · · · · · · · · · · · · · · · · · ·	
International Bureau (PCT Rule 17.2(a)).		an and national stage application from the
* Certified copies not received:		
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		e a reply complying with the requirements
4. A SUBSTITUTE OATH OR DECLARATION must be subminFORMAL PATENT APPLICATION (PTO-152) which give		
5. CORRECTED DRAWINGS (as "replacement sheets") mus	st be submitted.	
(a) I including changes required by the Notice of Draftspers	son's Patent Drawing Review	w (PTO-948) attached
1) hereto or 2) to Paper No./Mail Date		
(b) ☐ including changes required by the attached Examiner' Paper No./Mail Date	s Amendment / Comment o	r in the Office action of
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in t		
 DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT 		
Attachment(s) 1. ☑ Notice of References Cited (PTO-892)	5 Notice of In	oformal Patent Application (PTO-152)
Notice of Preferences Gled (P10-092) Notice of Draftperson's Patent Drawing Review (PTO-948)		ummary (PTO-413),
	Paper No.	/Mail Date
 Information Disclosure Statements (PTO-1449 or PTO/SB/C Paper No./Mail Date 	08), 7. ∐ Examiner's	Amendment/Comment
4. Examiner's Comment Regarding Requirement for Deposit of Biological Material Output Description: Description: Output Description: Des	8. ⊠ Examiner's 9. □ Other	Statement of Reasons for Allowance CARL WHITEHEAD, JR. SUPERVISORY PATENT EXAMINER
		TECHNOLOGY CENTER 2800

DETAILED ACTION

Allowable Subject Matter

Claims 1-21 are allowed.

The following is an examiner's statement of reasons for allowance:

Regarding claims 1-8, prior art does not teach or suggest, in combination with the other claimed limitations, forming a selective epitaxial layer on a top surface of a gate. As pointed out by Applicant in the arguments dated 9/28/2005, Roth et al. (U.S. 5.118.639) teaches forming an insulating layer covering the top surface of the gate, and then etching away the seed layer on the surface of the gate before forming the epitaxial layer. Therefore, the epitaxial layer does not form on the top surface of the gate. Additionally, Roth et al. does not teach forming the selective epitaxial growth seed layer pattern on a region including an active region on which a gate is formed. Roth et al. teaches forming the growth seed layer pattern only on the isolation regions (32 in Fig. 4).

Since claims 9-21 contain subject matter objected to in the Office action dated 6/27/2005 as being dependent upon rejected base claims but otherwise allowable if rewritten in independent form, claims 9-21 are allowed for reasons of record.

Specifically regarding claim 15, prior art does not teach or suggest, in combination with the other claimed limitations, using Si_xO_vN_z as a selective epitaxial growth (SEG) seed layer pattern. Roth et al. teaches using silicon as the SEG seed layer pattern, which Wolf et al. (Silicon Processing for the VLSI Era, vol. 1, 2000) teaches favors nucleation for selective epitaxial growth (p. 245). There is therefore no Art Unit: 2813

motivation to combine other relevant prior art with Roth et al. to arrive at the invention as claimed in claim 15.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Heather A. Doty, whose telephone number is 571-272-8429. The examiner can normally be reached on M-F, 8:30 - 5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead, Jr., can be reached at 571-272-1702. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

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